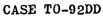
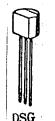
ELECTRONICS

N-CHANNEL SILICON FET

DESCRIPTION

2SK19 is N-channel silicon planar field effect transistor designed for FM tuner and VHF amplifier applications.





ABSOLUTE MAXIMUM RATINGS

VGDO	-18V
IG	10mA
Ptot	200mW
Tj,Tstg	$-55 \text{ to } +125^{\circ}\text{C}$
	IG Ptot

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX;	UNIT	TEST CONDITIONS	
Gate-Drain Breakdown Voltage	BVGDO	-18			V	IG=-100µA	
Gate Reverse Current	IGSS	, t		-10	nA	VGS=-1V V	DS=0
Zero-Gate Voltage Drain Current	IDSS *	3		24	mA.	V _{DS} =10V V	GS=0
Gate-Source Cutoff Voltage	VGS(off)	-1.2	-3	1	v	VDS=10V I	D=1\mu A
Forward ransadmittance	y _{fs}		5.5		mU	V _{BS=} 10V V f=1kHz	GS=0
Reverse Tunsfer Capacitance	Crss		0.45	0.65	pF	V _{GD} =-10V	f=1MHz

* According to the value of IDSS, 2SK19 is classified as follows.

2SK19-Y: 3-7

SSK19-GR : 6-14

2SK19-BL: 12-24



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